FOI	FORM PTO-1390  U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE Attorney's Docket No.:  TRANSMITTAL LETTER TO THE UNITED STATES  DESIGNATED/ELECTED OFFICE (DO/EO/US)  CONCERNING A FILING UNDER 35 U.S.C. 371  U.S. Appln. No.:							
INT	ERN.	ATIONAL APPLICATION NO. 97/02369	PRIORITY DATE CLAIMED					
		nvention ING GAS		-07, 2, 141, 00				
		t(s) for DO/EO/US Mitsushi						
App	licant	herewith submits to the United States Designation	ated/Elected Office (DO/EO/US) the following it	tems and other information:				
1.	$\boxtimes$	This is a FIRST submission of items concerning a filing under 35 U.S.C. 371.						
2.		This is a SECOND or SEBSEQUENT submission of items concerning a filing under 35 U.S.C. 371.						
3.	×	This express request to begin national examination procedures (35 U.S.C. 371(f)) at any time rather than delay examination until the expiration of the applicable time limit set in 35 U.S.C. 371(b) and PCT Articles 22 and 39(1).						
4.	$\boxtimes$	A proper Demand for International Prelimin	nary Examination was made by the 19th month fro	om the earliest claimed priority date.				
5.	$\boxtimes$	A copy of the International Application as f	filed (35 U.S.C. 371 (c)(2))					
	<ul> <li>a. ☐ is transmitted herewith (required only if not transmitted by the International Bureau).</li> <li>b. ☒ has been transmitted by the International Bureau.</li> <li>c. ☐ is not required, as the application was filed in the United States Receiving Office (RO/US)</li> </ul>							
6.	$\boxtimes$	A translation of the International Application into English (35 U.S.C. 371(c)(2)).						
7.	$\boxtimes$	Amendments to the claims of the International Application under PCT Article 19 (35 U.S.C. 371 (c)(3))						
		<ul> <li>a. ☐ are transmitted herewith (required only if not transmitted by the International Bureau).</li> <li>b. ☐ have been transmitted by the International Bureau.</li> <li>c. ☐ have not been made; however, the time limit for making such amendments had NOT expired.</li> <li>d. ☑ have not been made and will not be made.</li> </ul>						
8.		A translation of the amendments to the claim	ns under PCT Article 19 (35 U.S.C. 371(c)(3)).					
9.	$\boxtimes$	An oath or declaration of the inventor(s) (35	5 U.S.C. 371(c)(4)).					
10.		A translation of the annexes to the Internation	onal Preliminary Examination Report under PCT	Article 36 (35 U.S.C. 371(c)(5)).				
	Item	s 11. To 16. Below concern document(s) or	information included:					
11.		An Information Disclosure Statement und	ler 37 C.F.R. 1.97 and 1.98.					
12.	$\boxtimes$	An Assignment document for recording. A	separate cover sheet in compliance with 37 C F.	R. 2.28 and 3.31 is included.				
13.		A First preliminary amendment. A Second or subsequent preliminary amend	ment					
14.		A substitute specification.						
15.		A change of power of attorney and/or addre	ess letter.					
16		Other: Small Entity Statement						
1		Customer Number/Change of Address						
		A copy of the Notification of Missing Requi	rements under 35 U.S.C. 371.					
	In the event that a petition for extension of time is required to be submitted herewith, and in the event that a separate petition does not accompany this response, applicant hereby petitions under 37 CFR 1.136(a) for an extension of time of as many months as are required to render this submission timely. Any fee is authorized in 17(c).							
Date: 11 January 1000								

International Application No. PCT/JP97/02369

U.S. Application No. (if known, see 37 CFR 1.5)

Attomey's Docket No.: XI/P6217USO

Date: 11 January 1999

PTO use only

Calculations

	<b>a</b> 09/3				
IN THE UNITED STATES PATENT AND	300 Pee'd PUT/FTS	4	April 1	IDN 1	000
IN THE UNITED STATES PATENT AND	TŘAĎĚMAŘK OFFICE	ڪ	andro 1	Patent'	333

In re application of ITANO, M.	)		
New Application	) Atty's Dckt: X/P6217US		
Filed: On even date herewith	) Application Branch		
For: CLEANING GAS	)		

# PRELIMINARY AMENDMENT

Hon. Assistant Commissioner of Patents Washington, D.C. 20231

SIR:

Preliminary to the examination thereof, please amend the above-identified application as follows:

# IN THE CLAIMS:

Claim 5, lines 1 and 2, delete "any one of claims 1-4", and insert therefor --claim 1--. Claim 10, lines 1 and 2, delete "any one of claims 6-9", and insert therefor --claim 6--.

## REMARKS

The above amendments are being made in order to place the application in better condition for examination and to reduce the filing fee.

Favorable consideration is respectfully requested.

Respectfully submitted,

Date: January 11, 1999

By: Douglas E. Jackson Registration No. 28518

LARSON & TAYLOR

# DESCRIPTION

## CLEANING GAS

### TECHNICAL\_FIELD

The present invention relates to a cleaning gas suitable for use in production of semiconductors.

#### BACKGROUND ART

Perfluoro compounds such as  $\mathrm{CF_4}$ ,  $\mathrm{C_2F_6}$ ,  $\mathrm{C_4F_8}$  (perfluorocyclobutane) and  $\mathrm{SF_6}$  are used in large amounts as cleaning gases for plasma CVD chambers in production of semiconductors. Since the perfluoro compounds are stable and have long atomospheric lifetimes and high infrared absorbency, they have extremely high global warming potential (GWP) as compared with carbonic acid gas.  $\mathrm{CF_4}$  is 6300 times,  $\mathrm{C_2F_6}$  is 1250 times,  $\mathrm{C_4F_8}$  is 9100 times and  $\mathrm{SF_6}$  is 24900 times as high as carbonic acid gas in GWP. Therefore, development of a substitute gas having a low global warming potential is an urgent task.

An object of this invention is to provide a substitute gas which is suitable for use as a cleaning gas for plasma CVD chambers in production of semiconductors, the gas having a low global warming effect.

### DISCLOSURE OF INVENTION

The present invention provides the following cleaning gas and cleaning method:

5

10

15

20

25

10

15

20

25

1. A chamber cleaning gas comprising at least one gas selected from the group consisting of  $CF_3CF=CF_2$ ,  $CF_3CF-CF_2$  and  $CF_3C=0$ .

2. A chamber cleaning method comprising cleaning a plasma CVD chamber of a semiconductor integrated circuit production device using at least one gas selected from the group consisting of  $\text{CF}_3\text{CF}=\text{CF}_2$ ,  $\text{CF}_3\text{CF}-\text{CF}_2$  and  $\text{CF}_3\text{C}=0$ .

As the chamber cleaning gas of the invention, any of CF<sub>3</sub>CF=CF<sub>2</sub>, CF<sub>3</sub>CF-CF<sub>2</sub> and CF<sub>3</sub>C=O can be used; they can  $CF_3$ CF<sub>3</sub>

be used singly or in combination of two or more. The chamber cleaning gas of the invention may be used in combination with a monomer gas such as He, Ne, Ar,  $\rm H_2$ ,  $\rm N_2$  or  $\rm O_2$ .

There is no limitation on materials of the chamber. The chamber may be made of known materials such as stainless steel or aluminum alloy. Without adversely affecting the materials of the chamber, the chamber cleaning gas of the invention can quickly remove reaction byproducts attached to the wall of the chamber.

Examples of byproducts removed by the cleaning method of the invention are silicon, polysilicon, tungsten, titanium and their oxides, nitrides and

10

15

carbides.

As the chamber cleaning conditions of the invention, conventional conditions using perfluoro compounds may be used as they are.

All the three kinds of chamber cleaning gases of the invention have satisfactory levels of properties so that they can be used as substitutes for conventionally used chamber cleaning gasses, namely,  $\operatorname{CF}_4$ ,  $\operatorname{C}_2\operatorname{F}_6$  and  $\operatorname{SF}_6$ . Moreover, the gases of the invention have much lower global warming potential than  $\operatorname{CF}_4$ ,  $\operatorname{C}_2\operatorname{F}_6$  and  $\operatorname{SF}_6$ .

For example, when used under known chamber cleaning conditions (pressure = 100 m Torr; input high-frequency power = 300 W; gas flow rate = 50 cc/min) for 30 minutes,  $CF_3CF=CF_2$  of the invention fully and quickly removes attached byproducts from the chamber without damaging the chamber. Thus  $CF_3CF=CF_2$  of the invention is suitable for use in practice.

When 
$$\text{CF}_3\text{CF-CF}_2$$
 is used in place of  $\text{CF}_3\text{CF=CF}_2$ 

under the above conditions,  $CF_3CF-CF_2$  fully and quickly

removes attached byproducts from the chamber without damaging the chamber, thus being usable in practice.

Similarly, when  $CF_3C=0$  is used in place of  $CF_3$ 

 $\text{CF}_3\text{CF}=\text{CF}_2$ ,  $\text{CF}_3\text{C}=\text{O}$  fully and quickly removes attached  $\text{CF}_2$ 

byproducts from the chamber without damaging the chamber, thus being usable in practice.

According to the present invention, chamber cleaning can be done satisfactorily, without using any of  $CF_4$ ,  $C_2F_6$ ,  $C_4F_8$  and  $SF_6$  that have extremely high global warming potential as compared with carbonic acid gas.

10

#### CLAIMS

- 1. A chamber cleaning gas comprising at least one gas selected from the group consisting of  ${\rm CF_3CF=CF_2}$ ,  ${\rm CF_3CF-CF_2}$  and  ${\rm CF_3C=0}$ .
- 2. A chamber cleaning gas according to claim 1 comprising  $CF_3CF=CF_2$ .
- 3. A chamber cleaning gas according to claim 1 comprising hexafluoropropylene oxide represented by the formula  $\text{CF}_3\text{CF-CF}_2$ .
- 4. A chamber cleaning gas according to claim 1 comprising  $CF_3COCF_2$ .
- 5. A chamber cleaning gas according to any one of claims 1-4 which further comprises at least one monomer gas selected from the group consisting of He, Ne, Ar,  $\rm H_2$ ,  $\rm N_2$  and  $\rm O_2$ .
  - 6. A chamber cleaning method comprising the step of treating a plasma CVD chamber of a semiconductor integrated circuit production device with at least one
- integrated circuit production device with at least one chamber cleaning gas selected from the group consisting of  $CF_3CF=CF_2$ ,  $CF_3CF-CF_2$  and  $CF_3C=0$ .
- 7. A chamber cleaning method according to claim 6 wherein the chamber cleaning gas is  $CF_3CF=CF_2$ .

- 8. A chamber cleaning method according to claim 6 wherein the chamber cleaning gas is hexafluoropropylene oxide represented by the formula  $\text{CF}_3\text{CF-CF}_2$ .
- 9. A chamber cleaning method according to claim 6 wherein the chamber cleaning gas is  ${\rm CF_3COCF_3}$ .
  - 10. A chamber cleaning gas according to any one of claims 6-9 which further comprises at least one monomer gas selected from the group consisting of He, Ne, Ar,  $\rm H_2$ ,  $\rm N_2$  and  $\rm O_2$ .

## ABSTRACT

The present invention provides a chamber cleaning gas for Si film,  $\mathrm{Sio}_2$  film,  $\mathrm{Si}_3\mathrm{N}_4$  film or high-melting metal silicite film, the gas comprising at least one gas selected from the group consisting of  $\mathrm{CF}_3\mathrm{CF}\text{-}\mathrm{CF}_2$ ,  $\mathrm{CF}_3\mathrm{CF}\text{-}\mathrm{CF}_2$  and  $\mathrm{CF}_3\mathrm{CF}\text{-}\mathrm{O}$ , and provides a chamber cleaning  $\mathrm{CF}_3$ 

method.

3	(including Design and Natio	nal Stage PCT) Attorney's Dock	cet ID:				
As a below named inventor, I hereby declare that:  My residence, post office address and citizenship are as stated below adjacent to my name. I believe I am the original, first and sole inventor (if only one name is listed below) or an original first and identification of the subject matter which is claimed and for which a patent is country.							
on the invention entitled CLEANING GA	15	, the sp	ecification of which				
is attacked horsts. (or)		, utv sp	centeauon of which				
is attached hereto. (or)  X was filed on July 9, 1997							
		lended on					
as U.S. Application No.		(or)					
[ X] as International PCT Applicat	ion No. PCT/JP97/02369	<del></del>					
I hereby state that I have reviewed and understate to above. I acknowledge the duty to disclose	information which is material to paten	tability as defined in Title 37, Code of Federa	al Regulations, § 1.56.				
I hereby claim foreign priority benefits under Title 35, United States Code, § 119 (a) - (d) or §365 (b) of any foreign application(s) for patent or inventor's certificate, or §365 (a) of any PCT International application which designated at least one country other than the United States of America, listed below and have also identified below, where priority is not claimed, any foreign application for patent or inventor's certificate, or any PCT International application, having a filing date before that of the application on which priority is claimed:							
Prior Foreign Application(s) ( ADDIT	TONAL APPLICATIONS IDENTIFIED	O ON ATTACHED SHEET):					
Number	Country	Day/Month/Year Filed	Priority Not Claimed				
180518/1996	Japan	10/07/1996	•				
/ -							
thereby claim the benefit under Title 35, United the U.S., listed below; and insofar as the subject application in the manner provided by the first to patentability as defined in Title 37, Code of for PCT international filing date of this application.	I States Code, § 120 of any United States et matter of each of the claims of this a paragraph of Title 35, United States Co Federal Regulations § 1.56 which becam ation. — ADDITIONAL APPLICA	application(s), or §365(c) of any PCT Internat application is not disclosed in the prior United (e, § 112, I acknowledge the duty to disclose in a eavailable between the filing date of the prior TIONS IDENTIFIED ON ATTACHED SHE!	ional application designating States or PCT International aformation which is material application and the national ET.)				
Application Serial No.	Day/Month/Year Filed	Status patent	ed, pending, abandoned				
I hereby appoint the practitioners of LARSON	AND TAYLOR associated with the Cus	stomer Number provided below to prosecute th	is application and to transact				
all business in the Patent and Trademark Office			mer Number.				
	CUSTOMER NUMBI	-					
Direct all telephone calls to		, at TEL (703) 920-7200 (Fax: 703-8	92-8428)				
I hereby declare that all statements made here and further that these statements were made winder § 1001 of Title 18 of the United States Co	in of my own knowledge are true and t th the knowledge that willful false staten ode and that such willful false statements	hat all statements made on information and be nents and the like so made are punishable by fit may jeopardize the validity of the application	elief are believed to be true; ne or imprisonment, or both, or any patent issued thereon.				
Full Name of Sole TTAND Mitcush		Citizenship J	2020				
or First Inventor	-		apan				
Full Post Office Address C/O Yodogaw 1-1, Nishihitotsuya, Sett Residence - City, State/Country	a Seisakusho, DAIKIN I su-shi, Osaka 566, Jar	NDUSTRIES, LTD.,					
(if different from P.O. address)	as Post Office Address						
SIGN AND DATE HERE: Inventor's Signature:	Mitsushi Itano	Date: 4	Vov. 1998				
Full Name of Second	· · · · · · · · · · · · · · · · · · ·	Citizenship					
Joint Inventor, if any Full Post Office Address							
Residence - City, State/Country (if different from P.O. address)							
SIGN AND DATE HERE: Inventor's Signature:		Date:					
Full Name of Third		Citizenship					
Joint Inventor, if any Full Post Office Address	<del></del>						
Residence - City, State/Country (if different from P.O. address)							
SIGN AND DATE HERE: Inventor's Signature:		Date:					
Full Name of Fourth		Citizenship					
Joint Inventor, if any Full Post Office Address							
Residence - City, State/Country							
(if different from P.O. address)							
DATE HERE: Inventor's Signature:		Date:					

**DECLARATION FOR USA PATENT APPLICATION** 

14411